

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-3 (Canceled).

Claim 4 (Currently Amended): A protective barrier on a processing element utilized in a processing system for performing a process, comprising:

a bonding layer coupled to said processing element, wherein said bonding layer comprises a layer formed using plasma electrolytic oxidation and includes a transition layer, a primary layer, and an outer layer; and

a protective layer coupled to said bonding layer and configured to be exposed to said process, wherein said protective layer is coupled to said bonding layer after at least a portion of said outer layer is removed using at least one of polishing, grinding, and grit blasting.

Claim 5 (Original): The protective barrier as recited in claim [[1]]4, wherein said protective layer comprises a compound containing at least one of a III-column element and a Lanthanon element.

Claim 6 (Original): The protective barrier as recited in claim 5, wherein said III-column element comprises at least one of Yttrium, Scandium, and Lanthanum.

Claim 7 (Original): The protective barrier as recited in claim 5, wherein said Lanthanon element comprises at least one of Cerium, Dysprosium, and Europium.

Claim 8 (Currently Amended): The protective barrier as recited in claim [[1]]4,
wherein said protective layer comprises at least one of Al₂O₃, Yttria (Y₂O₃), Sc₂O₃, Sc₂F₃,
YF₃, La₂O₃, CeO₂, Eu₂O₃, and Dy₃O₃Dy₂O₃.

Claim 9 (Currently Amended): The protective barrier as recited in claim [[1]]4,
wherein the processing element comprises at least one of a metal, a silicon based material,
and a ceramic.

Claim 10 (Currently Amended): The protective barrier as recited in claim [[1]]4,
wherein the processing element comprises aluminum.

Claim 11 (Currently Amended): The protective barrier as recited in claim [[1]]4,
wherein the process comprises a plasma.

Claims 12-14 (Canceled).

Claim 15 (Previously Presented): A method of forming a protective barrier on a
processing element utilized in a processing system for performing a process comprising:
applying a bonding layer to said processing element, wherein said application of said
bonding layer comprises plasma electrolytic oxidation and said bonding layer comprises a
transition layer, a primary layer, and an outer layer; and
applying a protective layer to said bonding layer, wherein said outer layer is removed
using at least one of polishing, grinding, and grit blasting prior to applying the protective
layer.

Claim 16 (Currently Amended): The method as recited in claim [[12]]15, wherein said protective layer comprises a compound containing at least one of a III-column element and a Lanthanon element.

Claim 17 (Original): The method as recited in claim 16, wherein said III-column element comprises at least one of Yttrium, Scandium, and Lanthanum.

Claim 18 (Original): The method as recited in claim 16, wherein said Lanthanon element comprises at least one of Cerium, Dysprosium, and Europium.

Claim 19 (Currently Amended): The method as recited in claim [[12]]15, wherein said protective layer comprises at least one of Al₂O₃, Yttria (Y₂O₃), Sc₂O₃, Sc₂F₃, YF₃, La₂O₃, CeO₂, Eu₂O₃, and Dy₂O₃, Dy₃O₃.